

AMENDMENTS TO THE CLAIMS:

1. (Currently amended) A method, ~~applied to a microchip wafer~~, of removing pattern resist that remains after an etch of an underlying patterned layer ~~that is supported by a spacer layer~~, comprising the steps of:
 - providing a wafer having an etched patterned layer and an overlying mask pattern resist;
 - cleaning the wafer with a develop solution;
 - ashing the surface of the wafer; and
 - photochemically removing the pattern resist that remains after the cleaning and ashing steps.
2. (Original) The method of Claim 1, wherein the wafer is a micromechanical device wafer.
3. (Original) The method of Claim 1, wherein the wafer is a DMD wafer.
4. (Original) The method of Claim 1, wherein the cleaning step substantially removes polymer residue from the pattern resist.
5. (Original) The method of Claim 1, wherein the ashing step substantially removes hardened skin from the pattern resist.
6. (Original) The method of Claim 1, wherein the removing step is performed with an acetate strip process.
7. (Original) The method of Claim 1, wherein the patterned layer is a metal layer.
8. (Currently amended) A method of forming a patterned layer over a spacer layer on a wafer substrate, comprising the steps of:
 - depositing the spacer layer;
 - depositing material for the patterned layer;
 - depositing a pattern resist material;
 - ~~patterning the material for the patterned layer;~~
 - etching the resist material and the material for the patterned layer;
 - cleaning the wafer resist material and remaining material for the patterned layer
 - with a develop solution after said etching step;
 - ashing the surface of the wafer after said cleaning step; and

photochemically removing the pattern resist that remains after the cleaning and ashing steps.

9. (Original) The method of Claim 8, wherein the wafer is a micromechanical device wafer.
10. (Original) The method of Claim 8, wherein the wafer is a DMD wafer.
11. (Original) The method of Claim 8, wherein the cleaning step substantially removes polymer residue from the pattern resist.
12. (Original) The method of Claim 8, wherein the ashing step substantially removes hardened skin from the pattern resist.
13. (Original) The method of Claim 8, wherein the removing step is performed with an acetate strip process.
14. (Original) The method of Claim 8, wherein the patterned layer is a metal layer.
15. (Previously presented) A method of forming a micromirror array, comprising the steps of:
 - forming control circuitry on a semiconductor substrate;
 - depositing a first spacer layer on the substrate;
 - patterning the first spacer layer to define hinge support vias and spring tip support vias;
 - depositing a hinge layer over the first spacer layer;
 - forming at least one hinge etch mask on the hinge layer;
 - patterning the hinge layer to form at least one hinge, wherein the pattern is formed using a pattern resist layer and an etch process;
 - removing pattern resist that remains after the preceding step by: cleaning the wafer with a develop solution; ashing the surface of the wafer; and removing the pattern resist that remains after the cleaning and ashing steps;
 - depositing a second spacer layer over the hinge layer;
 - patterning the second spacer layer to define mirror support vias;
 - depositing a metal mirror layer over the second spacer layer;
 - patterning the metal mirror layer to form an array of micro mirrors; and
 - removing the first and the second spacer layers.
16. (Original) The method of Claim 15, wherein the cleaning step substantially removes

polymer residue from the pattern resist.

17. (Original) The method of Claim 15, wherein the ashing step substantially removes hardened skin from the pattern resist.
18. (Original) The method of Claim 15, wherein the removing step is performed with an acetate strip process.